## Christophe A Hurni

List of Publications by Year in descending order

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1162889 1474057 9 517 8 9 citations g-index h-index papers 9 9 9 752 docs citations times ranked citing authors all docs

#	Article	lF	CITATIONS
1	Bulk GaN flip-chip violet light-emitting diodes with optimized efficiency for high-power operation. Applied Physics Letters, 2015, 106, .	1.5	197
2	Design, fabrication, and performance analysis of GaN vertical electron transistors with a buried p/n junction. Applied Physics Letters, 2015, 106, .	1.5	81
3	Quantum Efficiency of III-Nitride Emitters: Evidence for Defect-Assisted Nonradiative Recombination and its Effect on the Green Gap. Physical Review Applied, 2019, 11, .	1.5	66
4	Electrical properties of III-Nitride LEDs: Recombination-based injection model and theoretical limits to electrical efficiency and electroluminescent cooling. Applied Physics Letters, 2016, 109, .	1.5	46
5	p-n junctions on Ga-face GaN grown by NH3 molecular beam epitaxy with low ideality factors and low reverse currents. Applied Physics Letters, 2010, 97, .	1.5	45
6	High light extraction efficiency in bulk-GaN based volumetric violet light-emitting diodes. Applied Physics Letters, 2014, 105, .	1.5	37
7	Effects of growth temperature on Mg-doped GaN grown by ammonia molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	29
8	Capacitance-voltage profiling on polar III-nitride heterostructures. Journal of Applied Physics, 2012, 112, .	1.1	10
9	m-plane $(101 \hat{A})$ and $(202 \hat{A}1)$ GaN/AlxGa1 $\hat{a}$ $\in$ "xN conduction band offsets measured by capacitance-voltage profiling. Applied Physics Letters, 2014, 105, .	1.5	6